UNISONIC TECHNOLOGIES CO., LTD

UTG75N65LLS1

Preliminary

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

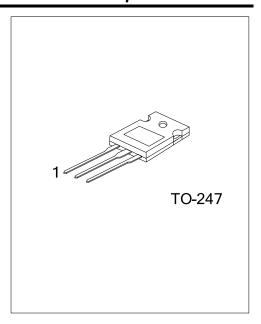
DESCRIPTION

The UTC **UTG75N65LLS1** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

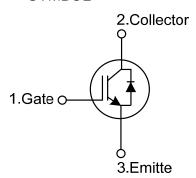
The UTC **UTG75N65LLS1** is suitable for the resonant or soft switching applications.

■ FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT),Typ.}$ = 1.52V @ I_C =75A, V_{GE} =15V (T_C =25°C)



■ SYMBOL



ORDERING INFORMATION

Ordering Number		Doolsogo	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package		2	3	Packing	
UTG75N65LLS1L-T47-T	UTG75N65LLS1G-T47-T	TO-247	G	С	Е	Tube	

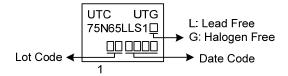
Note: Pin Assignment: G: Gate C: Collector E: Emitter

UTG75N65LLS1G-T47-T (1)Packing Type (1) T: Tube

(2)Package Type (2) T47: TO-247

(3)Green Package (3) G: Halogen Free and Lead Free, L: Lead Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V _{CES}	650	V
Gate-Emitter Voltage		V	±20	V
Transient Gate-emitter voltage (tp < 5 ms)		V_{GES}	±25	V
Continuous Collector Current	T _C =25°C	Ic	150	Α
	T _C =100°C		75	Α
Collector Current Pulsed (Note 1)		Ісм	300	Α
Diode Forward Current	T _C =25°C	l _F	150	Α
	T _C =100°C		75	Α
Short Circuit Withstand Time $V_{GE} = 15V, V_{CC} \le 200V$		tsc		
				μs
Allowed number of short circuits < 1000			8	
Time between short circuits: ≥1.0s T _{VJ} = 25°C				
Power Dissipation (T _C =25°C)		P _D	312	W
Operating Junction Temperature		T_J	-40 ~ +150	°C
Storage Temperature Range		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT	
Junction to Case	θјс	0.4	°C/W	

^{2.} Pulse width limited by maximum junction temperature.

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT
Off Characteristics	I.	•		L	I.		
Collector-Emitter Breakdown Voltage	BV _{CES}			650			V
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V				5	μΑ
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V				±400	nA
On Characteristics							
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}		4.0		7.0	V
Callantanta Fraittan Catamatian Valtana		I _C =75A, V _{GE} =15V	T _C =25°C		1.52	2.1	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}		T _C =125°C		2.0		V
Dynamic Characteristics		_		ā.	ā.		
Input Capacitance	C _{IES}			3930		рF	
Output Capacitance	C _{OES}	V _{CE} =25V, V _{GE} =0V, f=1MHz			333		рF
Reverse Transfer Capacitance	C _{RES}				72		рF
Switching Characteristics							
Total Gate Charge	Q_{G}			175		nC	
Gate-Emitter Charge	Q_GE	V _{CE} =520V, I _C =75A, V _{GE} =15V			44		nC
Gate-Collector Charge	Q_GC				90		nC
Turn-On Delay Time	t _{DON)}	V _{CC} =400V, I _C =75A, R _G =5Ω, V _{GE} =0~15V, L=500μH			28		ns
Rise Time	t _R				103		ns
Turn-Off Delay Time	t _{DOFF)}				131		ns
Fall Time	t _F				112		ns
Turn-On Switching Loss	Eon				4.31		mJ
Turn-Off Switching Loss	E _{OFF}			2.63		mJ	
SOURCE- DRAIN DIODE RATINGS AND	CHARACTE	RISTICS					
Forward Voltage Drop	V _F	I _F =75A				3.0	V
Reverse Recovery Time	t _{rr}	I _F =75A, dI/dt=100A/μS,			32		ns
Reverse Recovery Charge	Qrr	V _{CC} =400V			488		nC

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